



**128K X 36, 256K X 18
3.3V Synchronous SRAMs
3.3V I/O, Flow-Through Outputs
Burst Counter, Single Cycle Deselect**

**IDT71V3577
IDT71V3579**

Features

- ◆ 128K x 36, 256K x 18 memory configurations
- ◆ Supports fast access times:
 - Commercial:*
 - 7.5ns up to 117MHz clock frequency
 - Commercial and Industrial:*
 - 8.0ns up to 100MHz clock frequency
 - 8.5ns up to 87MHz clock frequency
- ◆ LBO input selects interleaved or linear burst mode
- ◆ Self-timed write cycle with global write control (\overline{GW}), byte write enable (\overline{BWE}), and byte writes (\overline{BW}_x)
- ◆ 3.3V core power supply
- ◆ Power down controlled by ZZ input
- ◆ 3.3V I/O
- ◆ Packaged in a JEDEC Standard 100-pin plastic thin quad flatpack (TQFP), 119 ball grid array (BGA) and 165 fine pitch ball grid array

Description

The IDT71V3577/79 are high-speed SRAMs organized as 128K x 36/256K x 18. The IDT71V3577/79 SRAMs contain write, data, address and control registers. There are no registers in the data output path (flow-through architecture). Internal logic allows the SRAM to generate a self-timed write based upon a decision which can be left until the end of the write cycle.

The burst mode feature offers the highest level of performance to the system designer, as the IDT71V3577/79 can provide four cycles of data for a single address presented to the SRAM. An internal burst address counter accepts the first cycle address from the processor, initiating the access sequence. The first cycle of output data will flow-through from the array after a clock-to-data access time delay from the rising clock edge of the same cycle. If burst mode operation is selected ($\overline{ADV}=\text{LOW}$), the subsequent three cycles of output data will be available to the user on the next three rising clock edges. The order of these three addresses are defined by the internal burst counter and the LBO input pin.

The IDT71V3577/79 SRAMs utilize IDT's latest high-performance CMOS process and are packaged in a JEDEC standard 14mm x 20mm 100-pin thin plastic quad flatpack (TQFP) as well as a 119 ball grid array (BGA) and a 165 fine pitch ball grid array (FBGA).

Pin Description Summary

A0-A17	Address Inputs	Input	Synchronous
\overline{CE}	Chip Enable	Input	Synchronous
$\overline{CS}_0, \overline{CS}_1$	Chip Selects	Input	Synchronous
\overline{OE}	Output Enable	Input	Asynchronous
\overline{GW}	Global Write Enable	Input	Synchronous
\overline{BWE}	Byte Write Enable	Input	Synchronous
$\overline{BW}_1, \overline{BW}_2, \overline{BW}_3, \overline{BW}_4^{(1)}$	Individual Byte Write Selects	Input	Synchronous
CLK	Clock	Input	N/A
\overline{ADV}	Burst Address Advance	Input	Synchronous
\overline{ADSC}	Address Status (Cache Controller)	Input	Synchronous
\overline{ADSP}	Address Status (Processor)	Input	Synchronous
\overline{LBO}	Linear / Interleaved Burst Order	Input	DC
ZZ	Sleep Mode	Input	Asynchronous
I/O0-I/O31, I/Op1-I/Op4	Data Input / Output	I/O	Synchronous
V _{DD} , V _{DDQ}	Core Power, I/O Power	Supply	N/A
V _{SS}	Ground	Supply	N/A

NOTE:

1. \overline{BW}_3 and \overline{BW}_4 are not applicable for the IDT71V3579.

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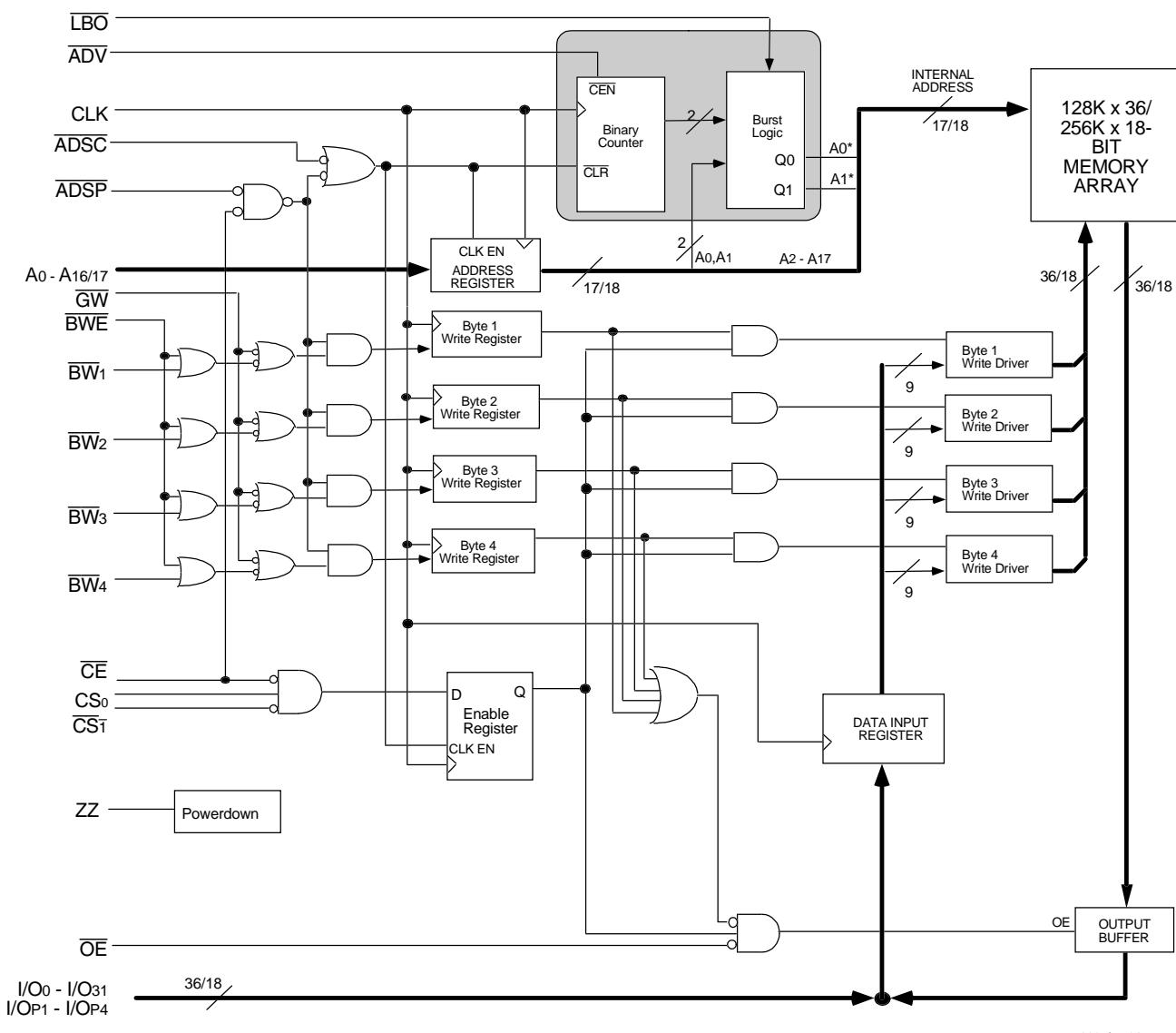
Pin Definitions⁽¹⁾

Symbol	Pin Function	I/O	Active	Description
A0-A17	Address Inputs	I	N/A	Synchronous Address inputs. The address register is triggered by a combination of the rising edge of CLK and ADSC Low or ADSP Low and CE Low.
ADSC	Address Status (Cache Controller)	I	LOW	Synchronous Address Status from Cache Controller. ADSC is an active LOW input that is used to load the address registers with new addresses.
ADSP	Address Status (Processor)	I	LOW	Synchronous Address Status from Processor. ADSP is an active LOW input that is used to load the address registers with new addresses. ADSP is gated by CE.
ADV	Burst Address Advance	I	LOW	Synchronous Address Advance. ADV is an active LOW input that is used to advance the internal burst counter, controlling burst access after the initial address is loaded. When the input is HIGH the burst counter is not incremented; that is, there is no address advance.
BWE	Byte Write Enable	I	LOW	Synchronous byte write enable gates the byte write inputs BW1-BW4. If BWE is LOW at the rising edge of CLK then BWx inputs are passed to the next stage in the circuit. If BWE is HIGH then the byte write inputs are blocked and only GW can initiate a write cycle.
BW1-BW4	Individual Byte Write Enables	I	LOW	Synchronous byte write enables. BW1 controls I/O0-7, I/Op1, BW2 controls I/O8-15, I/Op2, etc. Any active byte write causes all outputs to be disabled.
CE	Chip Enable	I	LOW	Synchronous chip enable. CE is used with CS0 and CS1 to enable the IDT71V3577/79. CE also gates ADSP.
CLK	Clock	I	N/A	This is the clock input. All timing references for the device are made with respect to this input.
CS0	Chip Select 0	I	HIGH	Synchronous active HIGH chip select. CS0 is used with CE and CS1 to enable the chip.
CS1	Chip Select 1	I	LOW	Synchronous active LOW chip select. CS1 is used with CE and CS0 to enable the chip.
GW	Global Write Enable	I	LOW	Synchronous global write enable. This input will write all four 9-bit data bytes when LOW on the rising edge of CLK. GW supersedes individual byte write enables.
I/O0-I/O31 I/Op1-I/Op4	Data Input/Output	I/O	N/A	Synchronous data input/output (I/O) pins. The data input path is registered, triggered by the rising edge of CLK. The data output path is flow-through (no output register).
LBO	Linear Burst Order	I	LOW	Asynchronous burst order selection input. When LBO is HIGH, the inter-leaved burst sequence is selected. When LBO is LOW the Linear burst sequence is selected. LBO is a static input and must not change state while the device is operating.
OE	Output Enable	I	LOW	Asynchronous output enable. When OE is LOW the data output drivers are enabled on the I/O pins if the chip is also selected. When OE is HIGH the I/O pins are in a high-impedance state.
VDD	Power Supply	N/A	N/A	3.3V core power supply.
VDDQ	Power Supply	N/A	N/A	3.3V I/O Supply.
Vss	Ground	N/A	N/A	Ground.
NC	No Connect	N/A	N/A	NC pins are not electrically connected to the device.
ZZ	Sleep Mode	1	HIGH	Asynchronous sleep mode input. ZZ HIGH will gate the CLK internally and power down the IDT71V3577/79 to its lowest power consumption level. Data retention is guaranteed in Sleep Mode.

NOTE:

1. All synchronous inputs must meet specified setup and hold times with respect to CLK.

Functional Block Diagram



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Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial Values	Unit
V _{TERM} ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
V _{TERM} ^(3,6)	Terminal Voltage with Respect to GND	-0.5 to V _{DD}	V
V _{TERM} ^(4,6)	Terminal Voltage with Respect to GND	-0.5 to V _{DD} +0.5	V
V _{TERM} ^(5,6)	Terminal Voltage with Respect to GND	-0.5 to V _{DDQ} +0.5	V
T _A ⁽⁷⁾	Commercial Operating Temperature	-0 to +70	°C
	Industrial Operating Temperature	-40 to +85	°C
T _{BIAS}	Temperature Under Bias	-55 to +125	°C
T _{STG}	Storage Temperature	-55 to +125	°C
P _T	Power Dissipation	2.0	W
I _{OUT}	DC Output Current	50	mA

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NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- V_{DD} terminals only.
- V_{DDQ} terminals only.
- Input terminals only.
- I/O terminals only.
- This is a steady-state DC parameter that applies after the power supplies have ramped up. Power supply sequencing is not necessary; however, the voltage on any input or I/O pin cannot exceed V_{DDQ} during power supply ramp up.
- T_A is the "instant on" case temperature.

100 Pin TQFP Capacitance (T_A = +25° C, f = 1.0mhz)

Symbol	Parameter ⁽¹⁾	Conditions	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 3dV	5	pF
C _{IO}	I/O Capacitance	V _{OUT} = 3dV	7	pF

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165 fBGA Capacitance (T_A = +25° C, f = 1.0mhz)

Symbol	Parameter ⁽¹⁾	Conditions	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 3dV	7	pF
C _{IO}	I/O Capacitance	V _{OUT} = 3dV	7	pF

NOTE:

- This parameter is guaranteed by device characterization, but not production tested.

Recommended Operating Temperature Supply Voltage

Grade	Temperature ⁽¹⁾	V _{SS}	V _{DD}	V _{DDQ}
Commercial	0°C to +70°C	0V	3.3V±5%	3.3V±5%
Industrial	-40°C to +85°C	0V	3.3V±5%	3.3V±5%

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NOTES:

- T_A is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Typ.	Max.	Unit
V _{DD}	Core Supply Voltage	3.135	3.3	3.465	V
V _{DDQ}	I/O Supply Voltage	3.135	3.3	3.465	V
V _{SS}	Supply Voltage	0	0	0	V
V _{IH}	Input High Voltage - Inputs	2.0	—	V _{DD} +0.3	V
V _{IH}	Input High Voltage - I/O	2.0	—	V _{DDQ} +0.3 ⁽¹⁾	V
V _{IL}	Input Low Voltage	-0.3 ⁽²⁾	—	0.8	V

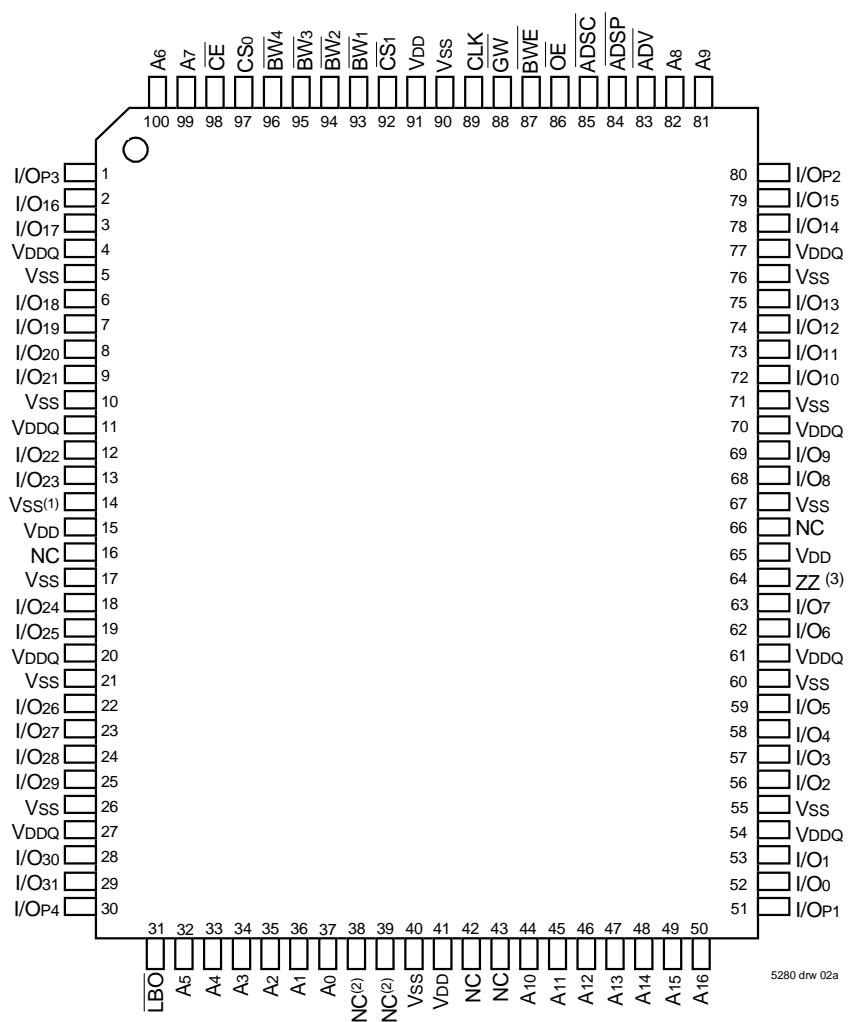
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- V_{IH} (max) = V_{DDQ} + 1.0V for pulse width less than t_{CYC/2}, once per cycle.
- V_{IL} (min) = -1.0V for pulse width less than t_{CYC/2}, once per cycle.

119 BGA Capacitance (T_A = +25° C, f = 1.0mhz)

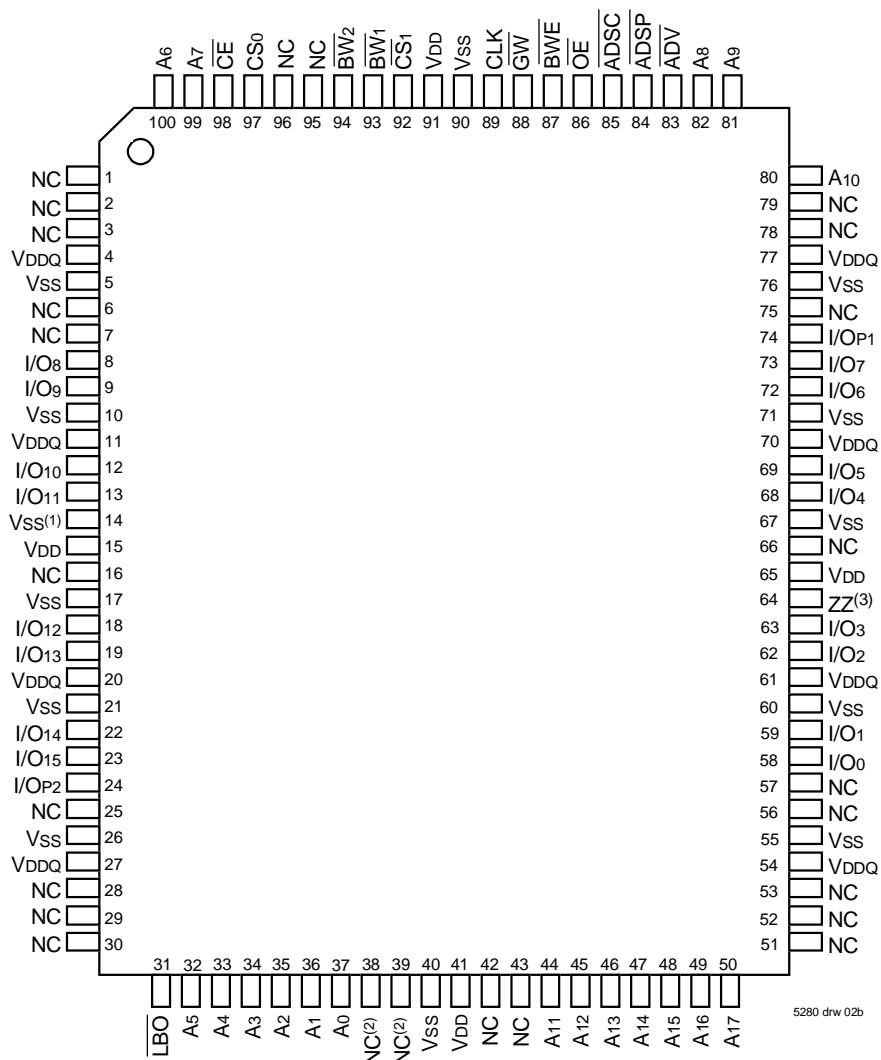
Symbol	Parameter ⁽¹⁾	Conditions	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 3dV	7	pF
C _{IO}	I/O Capacitance	V _{OUT} = 3dV	7	pF

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Pin Configuration – 128K x 36**100 TQFP
Top View****NOTES:**

1. Pin 14 does not have to be directly connected to Vss as long as the input voltage is $\leq V_{IL}$.
2. Pins 38 and 39 can be either NC or connected to Vss.
3. Pin 64 can be left unconnected and the device will always remain in active mode.

Pin Configuration – 256K x 18



100 TQFP
Top View

NOTES:

1. Pin 14 does not have to be directly connected to Vss as long as the input voltage is $\leq VIL$.
2. Pins 38 and 39 can be either NC or connected to Vss.
3. Pin 64 can be left unconnected and the device will always remain in active mode.

Pin Configuration – 128K x 36, 119 BGA

	1	2	3	4	5	6	7
A	VDDQ	A6	A4	ADSP	A8	A16	VDDQ
B	NC	CS ₀	A3	ADSC	A9	CS ₁	NC
C	NC	A7	A2	VDD	A12	A15	NC
D	I/O16	I/OP3	VSS	NC	VSS	I/OP2	I/O15
E	I/O17	I/O18	VSS	CE	VSS	I/O13	I/O14
F	VDDQ	I/O19	VSS	OE	VSS	I/O12	VDDQ
G	I/O20	I/O21	BW ³	ADV	BW ²	I/O11	I/O10
H	I/O22	I/O23	VSS	GW	VSS	I/O9	I/O8
J	VDDQ	VDD	NC	VDD	NC	VDD	VDDQ
K	I/O24	I/O26	VSS	CLK	VSS	I/O6	I/O7
L	I/O25	I/O27	BW ⁴	NC ⁽²⁾	BW ¹	I/O4	I/O5
M	VDDQ	I/O28	VSS	BWE	VSS	I/O3	VDDQ
N	I/O29	I/O30	VSS	A1	VSS	I/O2	I/O1
P	I/O31	I/OP4	VSS	A0	VSS	I/O0	I/OP1
R	NC	A5	LBO	VDD	VSS	A13	NC
T	NC	NC	A10	A11	A14	NC	ZZ ⁽³⁾
U	VDDQ	DNU ⁽⁴⁾	DNU ⁽⁴⁾	DNU ^(2,4)	DNU ⁽⁴⁾	DNU ⁽⁴⁾	VDDQ

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Top View

Pin Configuration – 256K x 18, 119 BGA

	1	2	3	4	5	6	7
A	VDDQ	A6	A4	ADSP	A8	A16	VDDQ
B	NC	CS ₀	A3	ADSC	A9	CS ₁	NC
C	NC	A7	A2	VDD	A13	A17	NC
D	I/O8	NC	VSS	NC	VSS	I/O7	NC
E	NC	I/O9	VSS	CE	VSS	NC	I/O6
F	VDDQ	NC	VSS	OE	VSS	I/O5	VDDQ
G	NC	I/O10	BW ²	ADV	VSS	NC	I/O4
H	I/O11	NC	VSS	GW	VSS	I/O3	NC
J	VDDQ	VDD	NC	VDD	NC	VDD	VDDQ
K	NC	I/O12	VSS	CLK	VSS	NC	I/O2
L	I/O13	NC	VSS	NC ⁽²⁾	BW ¹	I/O1	NC
M	VDDQ	I/O14	VSS	BWE	VSS	NC	VDDQ
N	I/O15	NC	VSS	A1	VSS	I/O0	NC
P	NC	I/OP2	VSS	A0	VSS	NC	I/OP1
R	NC	A5	LBO	VDD	VSS	A12	NC
T	NC	A10	A15	NC	A14	A11	ZZ ⁽³⁾
U	VDDQ	DNU ⁽⁴⁾	DNU ⁽⁴⁾	DNU ^(2,4)	DNU ⁽⁴⁾	DNU ⁽⁴⁾	VDDQ

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Top View

NOTES:

- R5 does not have to be directly connected to Vss as long as the input voltage is $\leq V_{IL}$.
- L4 and U4 can be either NC or connected to Vss.
- T7 can be left unconnected and the device will always remain in active mode.
- DNU = Do not use: Pins U2, U3, U4, U5 and U6 are reserved for respective JTAG pins: TDI, TDO, TMS, TCK and \overline{TRST} on future revisions. Within the current version these pins are not connected.

Pin Configuration – 128K x 36, 165 fBGA

	1	2	3	4	5	6	7	8	9	10	11
A	NC ⁽⁴⁾	A7	\overline{CE}_1	\overline{BW}_3	\overline{BW}_2	\overline{CS}_1	\overline{BWE}	\overline{ADSC}	\overline{ADV}	A8	NC
B	NC	A6	CS0	\overline{BW}_4	\overline{BW}_1	CLK	\overline{GW}	\overline{OE}	\overline{ADSP}	A9	NC ⁽⁴⁾
C	I/O ₃	NC	VDDQ	VSS	VSS	VSS	VSS	VSS	VDDQ	NC	I/O ₂
D	I/O ₁₇	I/O ₁₆	VDDQ	VDD	VSS	VSS	VSS	VDD	VDDQ	I/O ₁₅	I/O ₁₄
E	I/O ₁₉	I/O ₁₈	VDDQ	VDD	VSS	VSS	VSS	VDD	VDDQ	I/O ₁₃	I/O ₁₂
F	I/O ₂₁	I/O ₂₀	VDDQ	VDD	VSS	VSS	VSS	VDD	VDDQ	I/O ₁₁	I/O ₁₀
G	I/O ₂₃	I/O ₂₂	VDDQ	VDD	VSS	VSS	VSS	VDD	VDDQ	I/O ₉	I/O ₈
H	VSS ⁽¹⁾	NC ⁽²⁾	NC	VDD	VSS	VSS	VSS	VDD	NC	NC	ZZ ⁽³⁾
J	I/O ₂₅	I/O ₂₄	VDDQ	VDD	VSS	VSS	VSS	VDD	VDDQ	I/O ₇	I/O ₆
K	I/O ₂₇	I/O ₂₆	VDDQ	VDD	VSS	VSS	VSS	VDD	VDDQ	I/O ₅	I/O ₄
L	I/O ₂₉	I/O ₂₈	VDDQ	VDD	VSS	VSS	VSS	VDD	VDDQ	I/O ₃	I/O ₂
M	I/O ₃₁	I/O ₃₀	VDDQ	VDD	VSS	VSS	VSS	VDD	VDDQ	I/O ₁	I/O ₀
N	I/O ₄	NC	VDDQ	VSS	DNU ⁽⁵⁾	NC ⁽⁴⁾	NC ⁽²⁾	VSS	VDDQ	NC	I/O ₁
P	NC	NC ⁽⁴⁾	A5	A2	DNU ⁽⁵⁾	A1	DNU ⁽⁵⁾	A10	A13	A14	NC ⁽⁴⁾
R	\overline{LBO}	NC ⁽⁴⁾	A4	A3	DNU ⁽⁵⁾	A0	DNU ⁽⁵⁾	A11	A12	A15	A16

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Pin Configuration – 256K x 18, 165 fBGA

	1	2	3	4	5	6	7	8	9	10	11
A	NC ⁽⁴⁾	A7	\overline{CE}_1	\overline{BW}_2	NC	\overline{CS}_1	\overline{BWE}	\overline{ADSC}	\overline{ADV}	A8	A10
B	NC	A6	CS0	NC	\overline{BW}_1	CLK	\overline{GW}	\overline{OE}	\overline{ADSP}	A9	NC ⁽⁴⁾
C	NC	NC	VDDQ	VSS	VSS	VSS	VSS	VSS	VDDQ	NC	I/O ₁
D	NC	I/O ₈	VDDQ	VDD	VSS	VSS	VSS	VDD	VDDQ	NC	I/O ₇
E	NC	I/O ₉	VDDQ	VDD	VSS	VSS	VSS	VDD	VDDQ	NC	I/O ₆
F	NC	I/O ₁₀	VDDQ	VDD	VSS	VSS	VSS	VDD	VDDQ	NC	I/O ₅
G	NC	I/O ₁₁	VDDQ	VDD	VSS	VSS	VSS	VDD	VDDQ	NC	I/O ₄
H	VSS ⁽¹⁾	NC ⁽²⁾	NC	VDD	VSS	VSS	VSS	VDD	NC	NC	ZZ ⁽³⁾
J	I/O ₁₂	NC	VDDQ	VDD	VSS	VSS	VSS	VDD	VDDQ	I/O ₃	NC
K	I/O ₁₃	NC	VDDQ	VDD	VSS	VSS	VSS	VDD	VDDQ	I/O ₂	NC
L	I/O ₁₄	NC	VDDQ	VDD	VSS	VSS	VSS	VDD	VDDQ	I/O ₁	NC
M	I/O ₁₅	NC	VDDQ	VDD	VSS	VSS	VSS	VDD	VDDQ	I/O ₀	NC
N	I/O ₂	NC	VDDQ	VSS	DNU ⁽⁵⁾	NC ⁽⁴⁾	NC ⁽²⁾	VSS	VDDQ	NC	NC
P	NC	NC ⁽⁴⁾	A5	A2	DNU ⁽⁵⁾	A1	DNU ⁽⁵⁾	A11	A14	A15	NC ⁽⁴⁾
R	\overline{LBO}	NC ⁽⁴⁾	A4	A3	DNU ⁽⁵⁾	A0	DNU ⁽⁵⁾	A12	A13	A16	A17

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NOTES:

1. H1 does not have to be directly Vss as long as input voltage is $\leq V_{IL}$.
2. H2 and N7 can be either NC or connected to Vss.
3. H11 can be left unconnected and the device will always remain in active mode.
4. Pins P11, N6, B11, A1, R2 and P2 are reserved for 9M, 18M, 36M, 72M, 144M and 288M respectively.
5. DNU = Do not use; Pins P5, P7, R5, R7 and N5 are reserved for respective JTAG pins: TDI, TDO, TMS, TCK and \overline{TRST} on future revisions. Within the current version these pins are not connected.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range ($V_{DD} = 3.3V \pm 5\%$)

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
$ I_L $	Input Leakage Current	$V_{DD} = \text{Max.}, V_{IN} = 0V \text{ to } V_{DD}$	—	5	μA
$ I_L $	ZZ and \overline{LBO} Input Leakage Current ⁽¹⁾	$V_{DD} = \text{Max.}, V_{IN} = 0V \text{ to } V_{DD}$	—	30	μA
$ I_O $	Output Leakage Current	$V_{OUT} = 0V \text{ to } V_{DD}, \text{Device Deselected}$	—	5	μA
V_{OL}	Output Low Voltage	$I_{OL} = +8mA, V_{DD} = \text{Min.}$	—	0.4	V
V_{OH}	Output High Voltage	$I_{OH} = -8mA, V_{DD} = \text{Min.}$	2.4	—	V

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NOTE:

1. The \overline{LBO} pin will be internally pulled to V_{DD} if it is not actively driven in the application and the ZZ in will be internally pulled to V_{SS} if not actively driven.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range ⁽¹⁾

Symbol	Parameter	Test Conditions	7.5ns	8ns		8.5ns		Unit
			Com'l Only	Com'l	Ind	Com'l	Ind	
I_{DD}	Operating Power Supply Current	Device Selected, Outputs Open, $V_{DD} = \text{Max.}, V_{DDQ} = \text{Max.}, V_{IN} \geq V_{IH} \text{ or } \leq V_{IL}, f = f_{MAX}^{(2)}$	255	200	210	180	190	mA
I_{SB1}	CMOS Standby Power Supply Current	Device Deselected, Outputs Open, $V_{DD} = \text{Max.}, V_{DDQ} = \text{Max.}, V_{IN} \geq V_{HD} \text{ or } \leq V_{LD}, f = 0^{(2,3)}$	30	30	35	30	35	mA
I_{SB2}	Clock Running Power Supply Current	Device Deselected, Outputs Open, $V_{DD} = \text{Max.}, V_{DDQ} = \text{Max.}, V_{IN} \geq V_{HD} \text{ or } \leq V_{LD}, f = f_{MAX}^{(2,3)}$	90	85	95	80	90	mA
I_{ZZ}	Full Sleep Mode Supply Current	$ZZ \geq V_{HD}, V_{DD} = \text{Max.}$	30	30	35	30	35	mA

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NOTES:

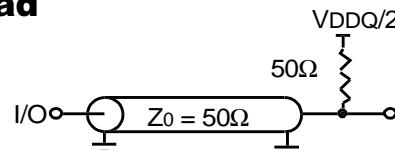
- All values are maximum guaranteed values.
- At $f = f_{MAX}$, inputs are cycling at the maximum frequency of read cycles of $1/t_{Cyc}$ while $\overline{ADSC} = \text{LOW}$; $f=0$ means no input lines are changing.
- For I/Os $V_{HD} = V_{DDQ} - 0.2V, V_{LD} = 0.2V$. For other inputs $V_{HD} = V_{DD} - 0.2V, V_{LD} = 0.2V$.

AC Test Conditions ($V_{DDQ} = 3.3V$)

Input Pulse Levels	0 to 3V
Input Rise/Fall Times	2ns
Input Timing Reference Levels	1.5V
Output Timing Reference Levels	1.5V
AC Test Load	See Figure 1

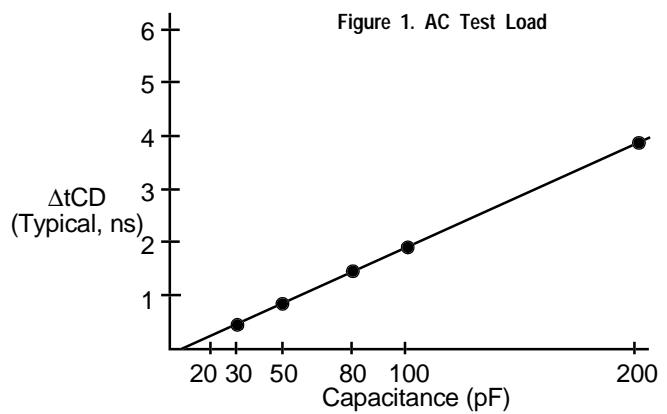
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AC Test Load



5280 drw 03

Figure 1. AC Test Load



5280 drw 05

Figure 2. Lumped Capacitive Load, Typical Derating

Synchronous Truth Table (1,3)

Operation	Address Used	\overline{CE}	CS_0	\overline{CS}_1	$ADSP$	$ADSC$	ADV	\overline{GW}	BWE	BWx	$\overline{OE}^{(2)}$	CLK	I/O
Deselected Cycle, Power Down	None	H	X	X	X	L	X	X	X	X	X	\uparrow	Hi-Z
Deselected Cycle, Power Down	None	L	X	H	L	X	X	X	X	X	X	\uparrow	Hi-Z
Deselected Cycle, Power Down	None	L	L	X	L	X	X	X	X	X	X	\uparrow	Hi-Z
Deselected Cycle, Power Down	None	L	X	H	X	L	X	X	X	X	X	\uparrow	Hi-Z
Deselected Cycle, Power Down	None	L	L	X	X	L	X	X	X	X	X	\uparrow	Hi-Z
Read Cycle, Begin Burst	External	L	H	L	L	X	X	X	X	X	L	\uparrow	Dout
Read Cycle, Begin Burst	External	L	H	L	L	X	X	X	X	X	H	\uparrow	Hi-Z
Read Cycle, Begin Burst	External	L	H	L	H	L	X	H	H	X	L	\uparrow	Dout
Read Cycle, Begin Burst	External	L	H	L	H	L	X	H	L	H	L	\uparrow	Dout
Read Cycle, Begin Burst	External	L	H	L	H	L	X	H	L	H	H	\uparrow	Hi-Z
Write Cycle, Begin Burst	External	L	H	L	H	L	X	H	L	L	X	\uparrow	Din
Write Cycle, Begin Burst	External	L	H	L	H	L	X	L	X	X	X	\uparrow	Din
Read Cycle, Continue Burst	Next	X	X	X	H	H	L	H	H	X	L	\uparrow	Dout
Read Cycle, Continue Burst	Next	X	X	X	H	H	L	H	H	X	H	\uparrow	Hi-Z
Read Cycle, Continue Burst	Next	X	X	X	H	H	L	H	X	H	L	\uparrow	Dout
Read Cycle, Continue Burst	Next	X	X	X	H	H	L	H	X	H	H	\uparrow	Hi-Z
Read Cycle, Continue Burst	Next	H	X	X	X	H	L	H	H	X	L	\uparrow	Dout
Read Cycle, Continue Burst	Next	H	X	X	X	H	L	H	H	X	H	\uparrow	Hi-Z
Read Cycle, Continue Burst	Next	H	X	X	X	H	L	H	H	X	H	\uparrow	Dout
Read Cycle, Continue Burst	Next	H	X	X	X	H	L	H	H	X	H	\uparrow	Hi-Z
Read Cycle, Continue Burst	Next	H	X	X	X	H	L	H	H	X	H	\uparrow	Dout
Read Cycle, Continue Burst	Next	H	X	X	X	H	L	H	H	X	H	\uparrow	Hi-Z
Write Cycle, Continue Burst	Next	X	X	X	H	H	L	H	L	L	X	\uparrow	Din
Write Cycle, Continue Burst	Next	X	X	X	H	H	L	L	X	X	X	\uparrow	Din
Write Cycle, Continue Burst	Next	H	X	X	X	H	L	H	L	L	X	\uparrow	Din
Write Cycle, Continue Burst	Next	H	X	X	X	H	L	L	X	X	X	\uparrow	Din
Read Cycle, Suspend Burst	Current	X	X	X	H	H	H	H	H	X	L	\uparrow	Dout
Read Cycle, Suspend Burst	Current	X	X	X	H	H	H	H	H	X	H	\uparrow	Hi-Z
Read Cycle, Suspend Burst	Current	X	X	X	H	H	H	H	X	H	L	\uparrow	Dout
Read Cycle, Suspend Burst	Current	X	X	X	H	H	H	H	X	H	H	\uparrow	Hi-Z
Read Cycle, Suspend Burst	Current	H	X	X	X	H	H	H	H	X	L	\uparrow	Dout
Read Cycle, Suspend Burst	Current	H	X	X	X	H	H	H	H	X	H	\uparrow	Hi-Z
Read Cycle, Suspend Burst	Current	H	X	X	X	H	H	H	H	X	H	\uparrow	Dout
Read Cycle, Suspend Burst	Current	H	X	X	X	H	H	H	H	X	H	\uparrow	Hi-Z
Write Cycle, Suspend Burst	Current	X	X	X	H	H	H	H	L	L	X	\uparrow	Din
Write Cycle, Suspend Burst	Current	X	X	X	H	H	H	L	X	X	X	\uparrow	Din
Write Cycle, Suspend Burst	Current	H	X	X	X	H	H	H	L	L	X	\uparrow	Din
Write Cycle, Suspend Burst	Current	H	X	X	X	H	H	H	L	X	X	\uparrow	Din
Write Cycle, Suspend Burst	Current	H	X	X	X	H	H	H	L	X	X	\uparrow	Din

NOTES:

1. L = V_{IL} , H = V_{IH} , X = Don't Care.
2. \overline{OE} is an asynchronous input.
3. ZZ - low for the table.

5280 tbt 11

Synchronous Write Function Truth Table (1, 2)

Operation	\overline{GW}	\overline{BWE}	\overline{BW}_1	\overline{BW}_2	\overline{BW}_3	\overline{BW}_4
Read	H	H	X	X	X	X
Read	H	L	H	H	H	H
Write all Bytes	L	X	X	X	X	X
Write all Bytes	H	L	L	L	L	L
Write Byte 1 ⁽³⁾	H	L	L	H	H	H
Write Byte 2 ⁽³⁾	H	L	H	L	H	H
Write Byte 3 ⁽³⁾	H	L	H	H	L	H
Write Byte 4 ⁽³⁾	H	L	H	H	H	L

5280 tbl 12

NOTES:

1. L = V_{IL} , H = V_{IH} , X = Don't Care.
2. \overline{BW}_3 and \overline{BW}_4 are not applicable for the IDT71V3579.
3. Multiple bytes may be selected during the same cycle.

Asynchronous Truth Table (1)

Operation ⁽²⁾	\overline{OE}	\overline{ZZ}	I/O Status	Power
Read	L	L	Data Out	Active
Read	H	L	High-Z	Active
Write	X	L	High-Z – Data In	Active
Deselected	X	L	High-Z	Standby
Sleep Mode	X	H	High-Z	Sleep

5280 tbl 13

NOTES:

1. L = V_{IL} , H = V_{IH} , X = Don't Care.
2. Synchronous function pins must be biased appropriately to satisfy operation requirements.

Interleaved Burst Sequence Table ($LBO=VDD$)

	Sequence 1		Sequence 2		Sequence 3		Sequence 4	
	A1	A0	A1	A0	A1	A0	A1	A0
First Address	0	0	0	1	1	0	1	1
Second Address	0	1	0	0	1	1	1	0
Third Address	1	0	1	1	0	0	0	1
Fourth Address ⁽¹⁾	1	1	1	0	0	1	0	0

5280 tbl 14

NOTE:

1. Upon completion of the Burst sequence the counter wraps around to its initial state.

Linear Burst Sequence Table ($LBO=Vss$)

	Sequence 1		Sequence 2		Sequence 3		Sequence 4	
	A1	A0	A1	A0	A1	A0	A1	A0
First Address	0	0	0	1	1	0	1	1
Second Address	0	1	1	0	1	1	0	0
Third Address	1	0	1	1	0	0	0	1
Fourth Address ⁽¹⁾	1	1	0	0	0	1	1	0

5280 tbl 15

NOTE:

1. Upon completion of the Burst sequence the counter wraps around to its initial state.

AC Electrical Characteristics**($V_{DD} = 3.3V \pm 5\%$, Commercial and Industrial Temperature Ranges)**

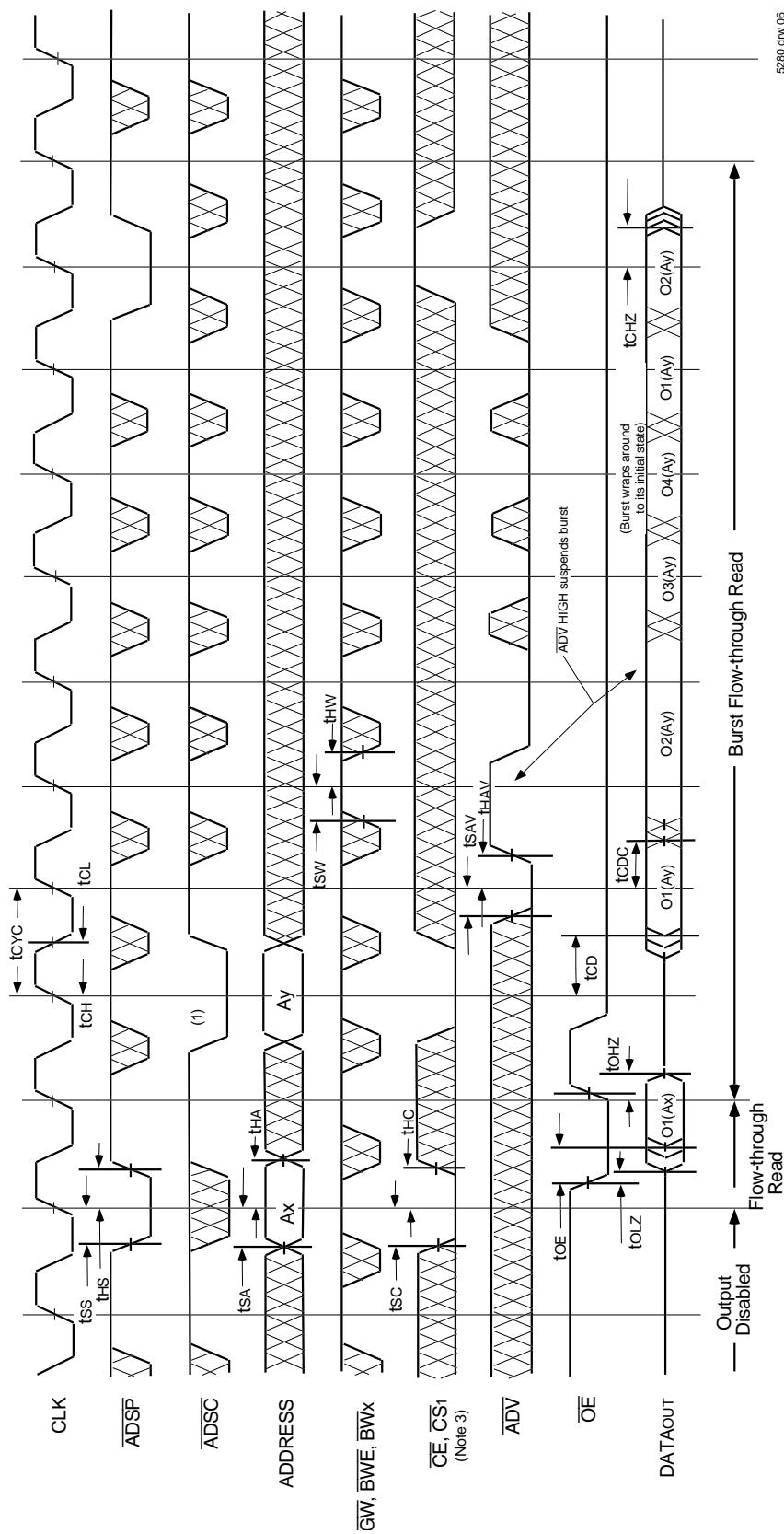
Symbol	Parameter	7.5ns ⁽⁵⁾		8ns		8.5ns		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
Clock Parameter								
t _{CYC}	Clock Cycle Time	8.5	—	10	—	11.5	—	ns
t _{CH} ⁽¹⁾	Clock High Pulse Width	3	—	4	—	4.5	—	ns
t _{CL} ⁽¹⁾	Clock Low Pulse Width	3	—	4	—	4.5	—	ns
Output Parameters								
t _{CD}	Clock High to Valid Data	—	7.5	—	8	—	8.5	ns
t _{CDC}	Clock High to Data Change	2	—	2	—	2	—	ns
t _{OLZ} ⁽²⁾	Clock High to Output Active	0	—	0	—	0	—	ns
t _{CHZ} ⁽²⁾	Clock High to Data High-Z	2	3.5	2	3.5	2	3.5	ns
t _{OE}	Output Enable Access Time	—	3.5	—	3.5	—	3.5	ns
t _{OLZ} ⁽²⁾	Output Enable Low to Output Active	0	—	0	—	0	—	ns
t _{OHZ} ⁽²⁾	Output Enable High to Output High-Z	—	3.5	—	3.5	—	3.5	ns
Set Up Times								
t _{SA}	Address Setup Time	1.5	—	2	—	2	—	ns
t _{SS}	Address Status Setup Time	1.5	—	2	—	2	—	ns
t _{SD}	Data In Setup Time	1.5	—	2	—	2	—	ns
t _{SW}	Write Setup Time	1.5	—	2	—	2	—	ns
t _{SAV}	Address Advance Setup Time	1.5	—	2	—	2	—	ns
t _{SC}	Chip Enable/Select Setup Time	1.5	—	2	—	2	—	ns
Hold Times								
t _{HA}	Address Hold Time	0.5	—	0.5	—	0.5	—	ns
t _{HS}	Address Status Hold Time	0.5	—	0.5	—	0.5	—	ns
t _{HD}	Data In Hold Time	0.5	—	0.5	—	0.5	—	ns
t _{HW}	Write Hold Time	0.5	—	0.5	—	0.5	—	ns
t _{HAV}	Address Advance Hold Time	0.5	—	0.5	—	0.5	—	ns
t _{HC}	Chip Enable/Select Hold Time	0.5	—	0.5	—	0.5	—	ns
Sleep Mode and Configuration Parameters								
t _{ZZPW}	ZZ Pulse Width	100	—	100	—	100	—	ns
t _{ZZR} ⁽³⁾	ZZ Recovery Time	100	—	100	—	100	—	ns
t _{CFG} ⁽⁴⁾	Configuration Set-up Time	34	—	40	—	50	—	ns

NOTES:

1. Measured as HIGH above V_{IH} and LOW below V_{IL} .
2. Transition is measured $\pm 200mV$ from steady-state.
3. Device must be deselected when powered-up from sleep mode.
4. t_{CFG} is the minimum time required to configure the device based on the \overline{LBO} input. \overline{LBO} is a static input and must not change during normal operation.
5. Commercial temperature range only.

5280tbl 16

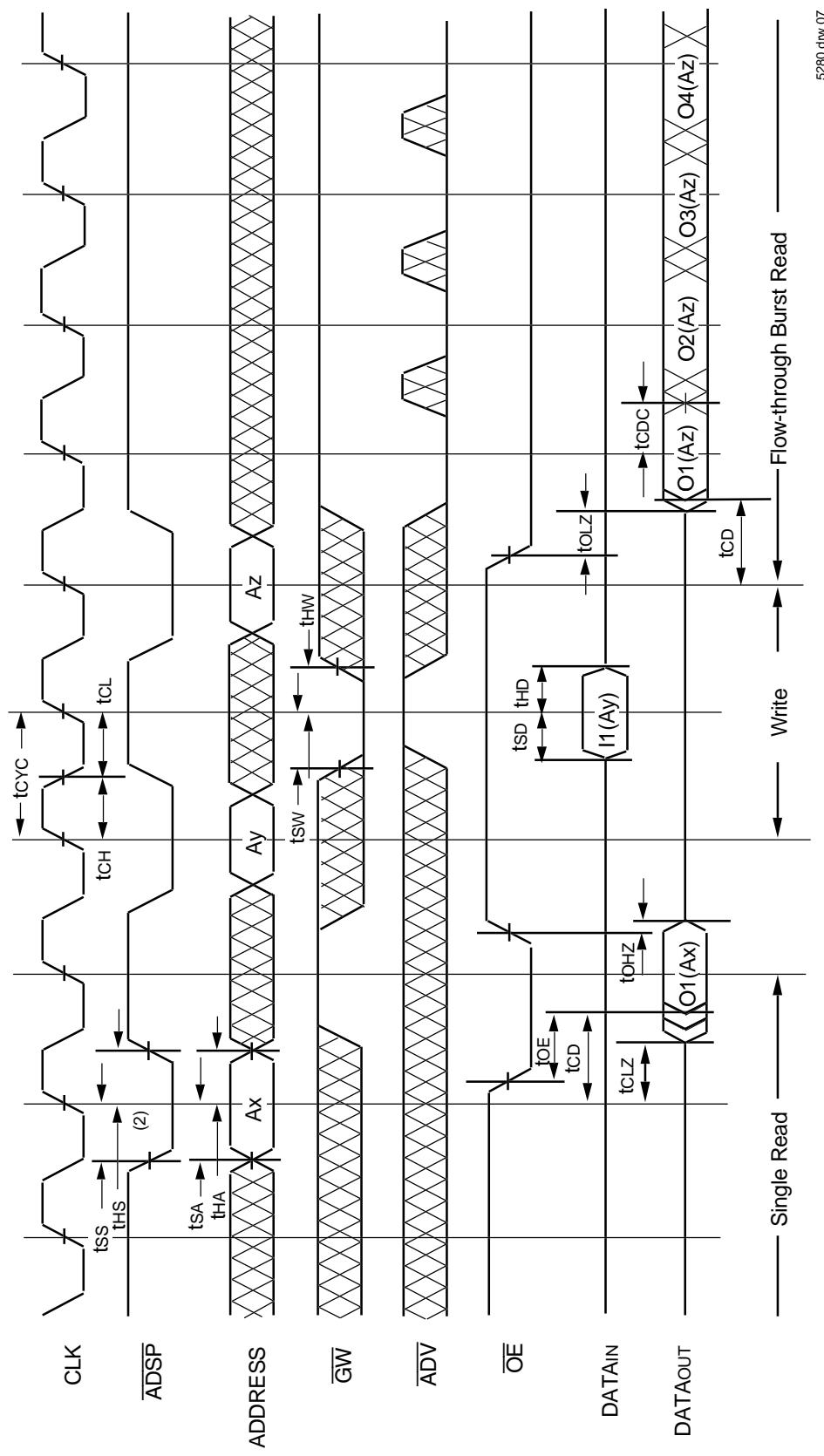
Timing Waveform of Flow-Through Read Cycle (1,2)



NOTES:

1. O1(Ax) represents the first output from the external address Ax. O1(Ay) represents the first output from the external address Ay. O2(Ay) represents the next output data in the burst sequence of the base address Ay, etc. where A0 and A1 are advancing for the four word burst in the sequence defined by the state of the \overline{LBO} input.
2. ZZ input is LOW and \overline{LBO} is Don't Care for this cycle.
3. CS0 timing transitions are identical but inverted to the \overline{CE} and \overline{CS}_1 signals. For example, when \overline{CE} and \overline{CS}_1 are LOW on this waveform, CS0 is HIGH.

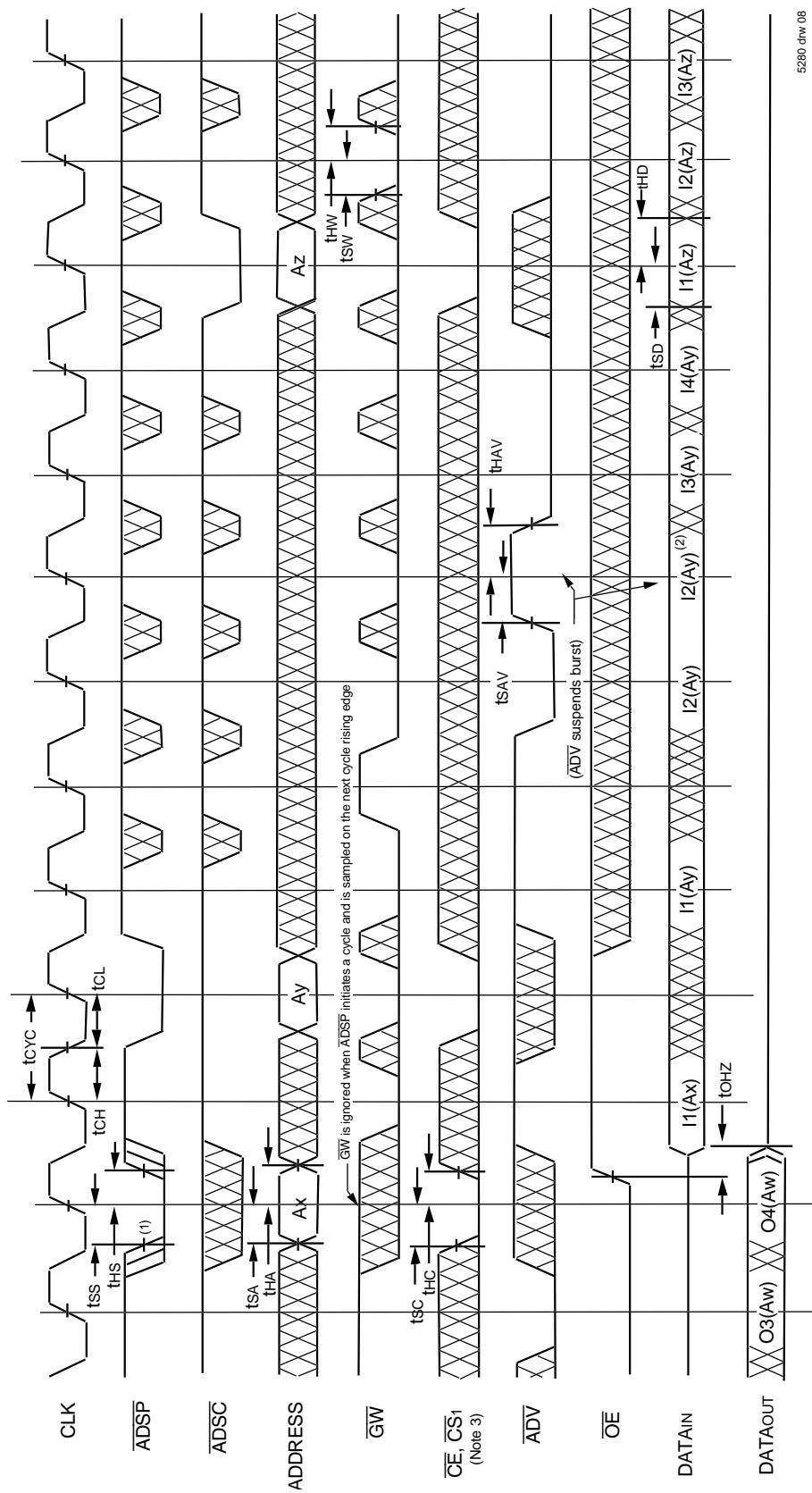
Timing Waveform of Combined Flow-Through Read and Write Cycles ^(1,2,3)



NOTES:

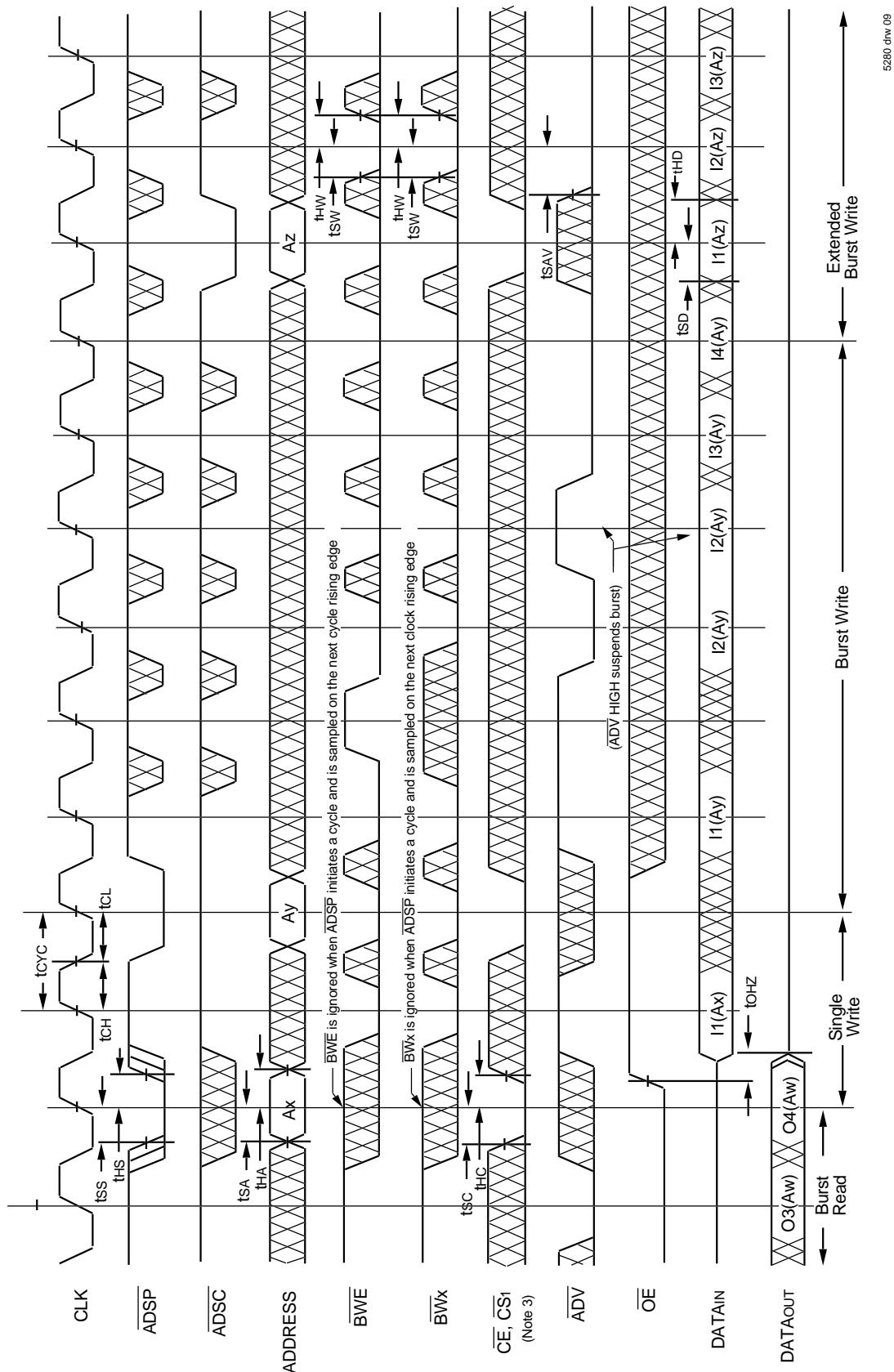
1. Device is selected through entire cycle; \overline{CE} and \overline{CS}_1 are LOW, CS_0 is HIGH.
2. Z_Z input is LOW and LBO is Don't Care for this cycle.
3. $O1(Ay)$ represents the first output from the external address Ay ; $O1(Az)$ represents the next output data in the burst sequence of the base address Az , etc. where $A0$ and $A1$ are advancing for the four word burst in the sequence defined by the state of the LBO input.

Timing Waveform of Write Cycle No. 1 - \overline{GW} Controlled ^(1,2,3)



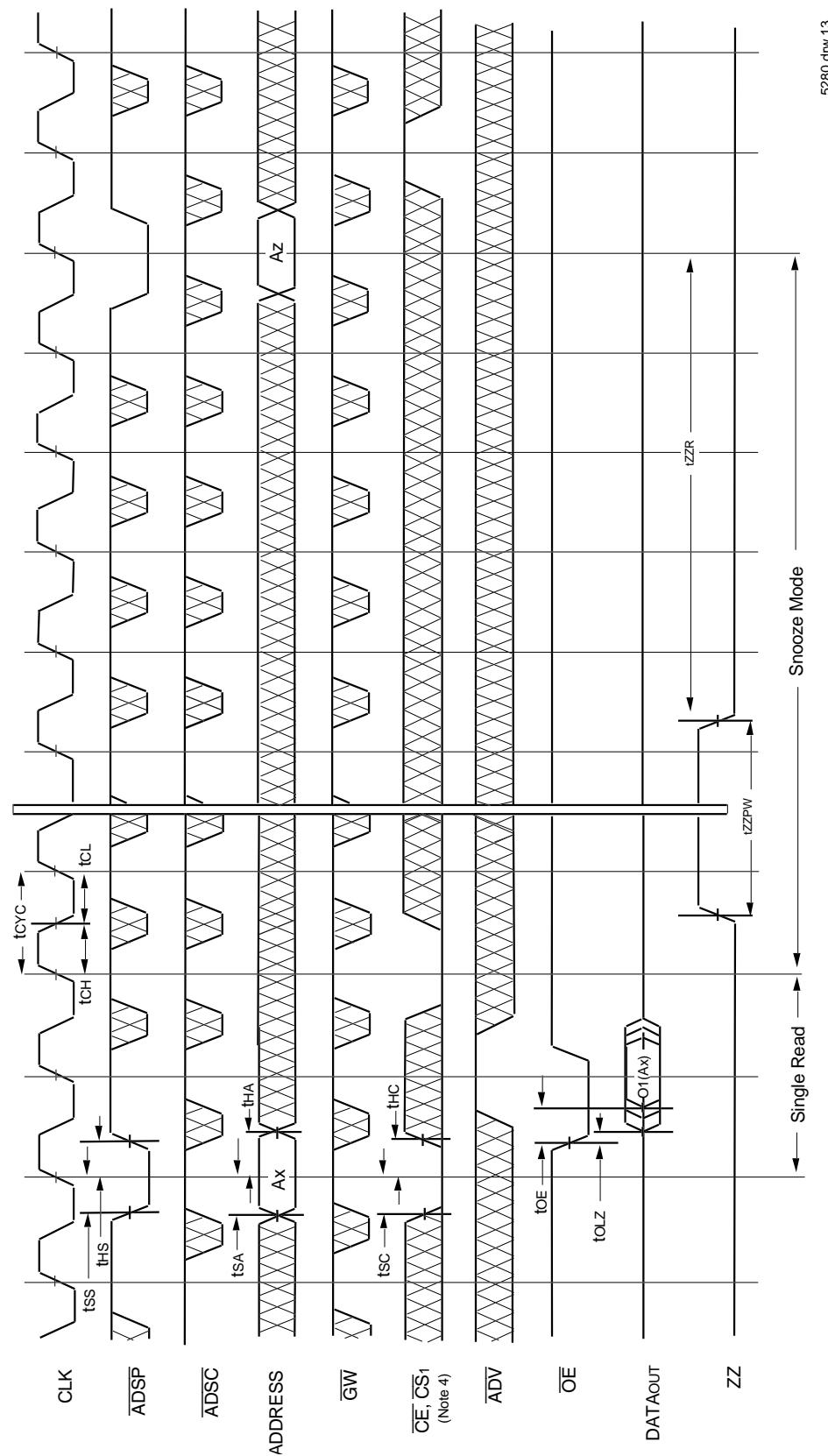
NOTES:

1. ZZ input is LOW, \overline{BWE} is HIGH and \overline{LBO} is Don't Care for this cycle.
 2. 04(Aw) represents the final output data in the burst sequence of the base address Aw. 11(Ax) represents the first input from the external address Ax. 11(Ax) represents the first input from the external address Aw. 11(Ax) represents the first input from the external address Ay. etc. where A0 and A1 are advancing for the four word bursts in the sequence defined by the state of the \overline{LBO} input. In the case of input 12(Ay) this data is valid for two cycles because \overline{ADV} is high and has suspended the burst.
 3. CS(latching transitions are identical but inverted to the \overline{CE} and $\overline{CS1}$ signals. For example, when \overline{CE} and $\overline{CS1}$ are LOW on this waveform, CS0 is HIGH.

Timing Waveform of Write Cycle No. 2 - Byte Controlled (1,2,3)**NOTES:**

1. ZZ input is LOW, \overline{GW} is HIGH and $\overline{LB0}$ is Don't Care for this cycle.
2. O4 (Aw) represents the final output data in the burst sequence of the base address Aw. I1 (Ay) represents the first input from the external address Ax. I1 (Ay) represents the first input from the external address Ay. I2 (Ay) represents the next input from the base address Ay, etc. where A0 and A1 are advancing for the four word burst in the sequence defined by the state of the $\overline{LB0}$ input. In the case of input I2 (Ay) this data is valid for two cycles because \overline{ADV} is high and has suspended the burst.
3. CS₁ timing transitions are identical but inverted to the CE and CS₁ signals. For example, when CE and CS₁ are LOW on this waveform, CS₁ is HIGH.

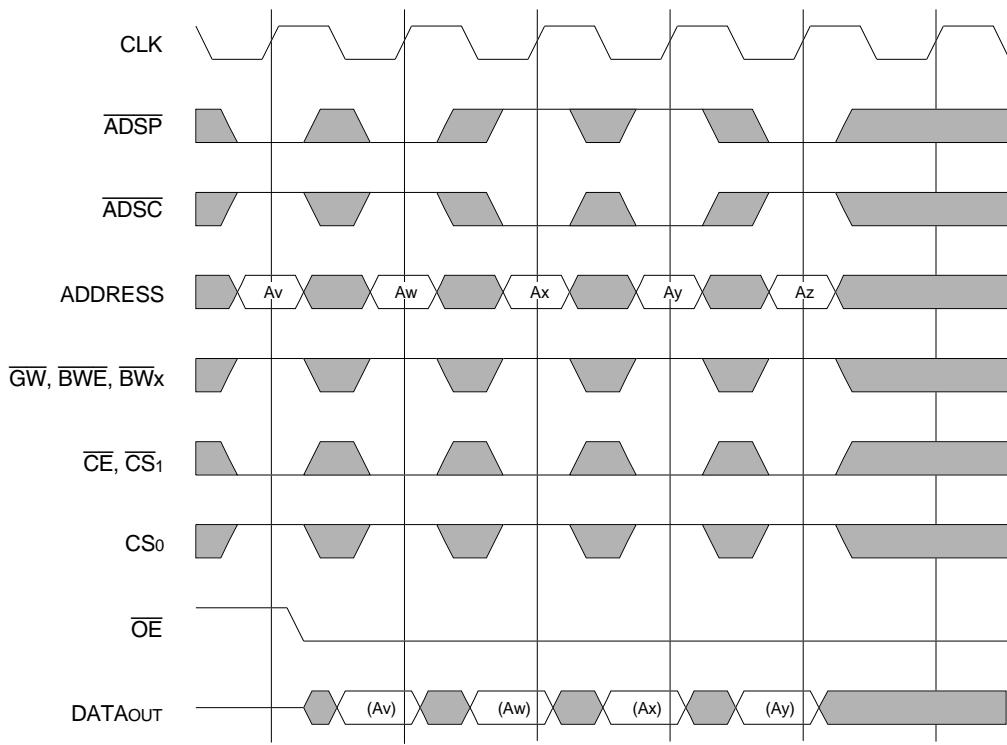
Timing Waveform of Sleep (ZZ) and Power-Down Modes^(1,2,3)



NOTES:

1. Device must power up in deselected Mode.
2. $\overline{[B\bar{O}]}$ is Don't Care for this cycle.
3. It is not necessary to retain the state of the input registers throughout the Power-down cycle.
4. CS0 timing transitions are identical but inverted to the \overline{CE} and $\overline{CS1}$ signals. For example, when CE and $CS1$ are LOW on this waveform, $CS0$ is HIGH.

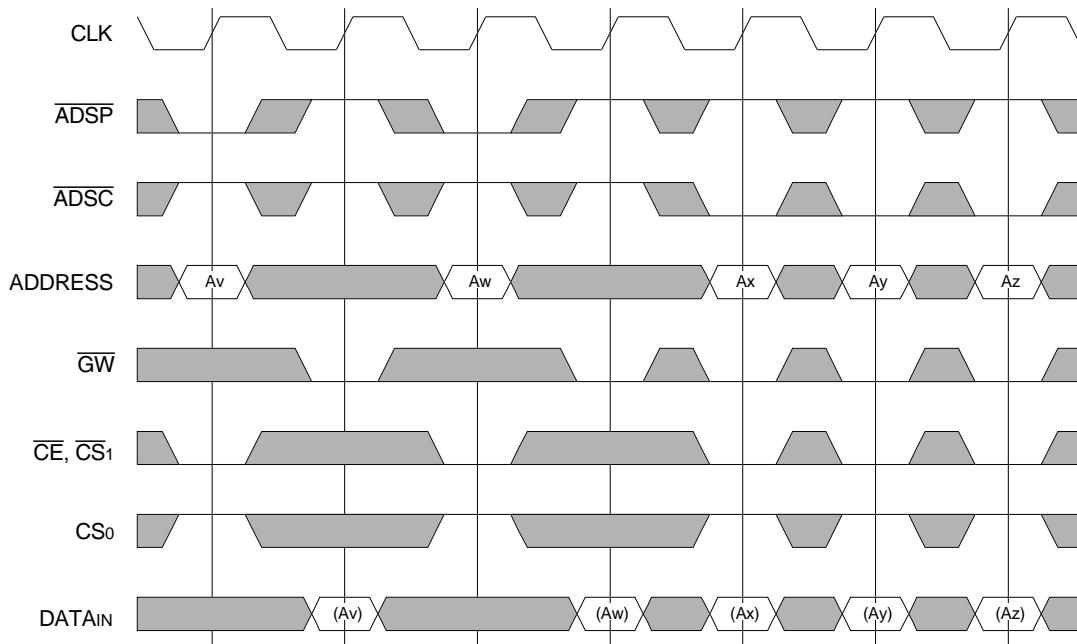
Non-Burst Read Cycle Timing Waveform



NOTES:

1. ZZ input is LOW, \overline{ADV} is HIGH and \overline{LBO} is Don't Care for this cycle.
2. (Ax) represents the data for address Ax, etc.
3. For read cycles, \overline{ADSP} and \overline{ADSC} function identically and are therefore interchangeable.

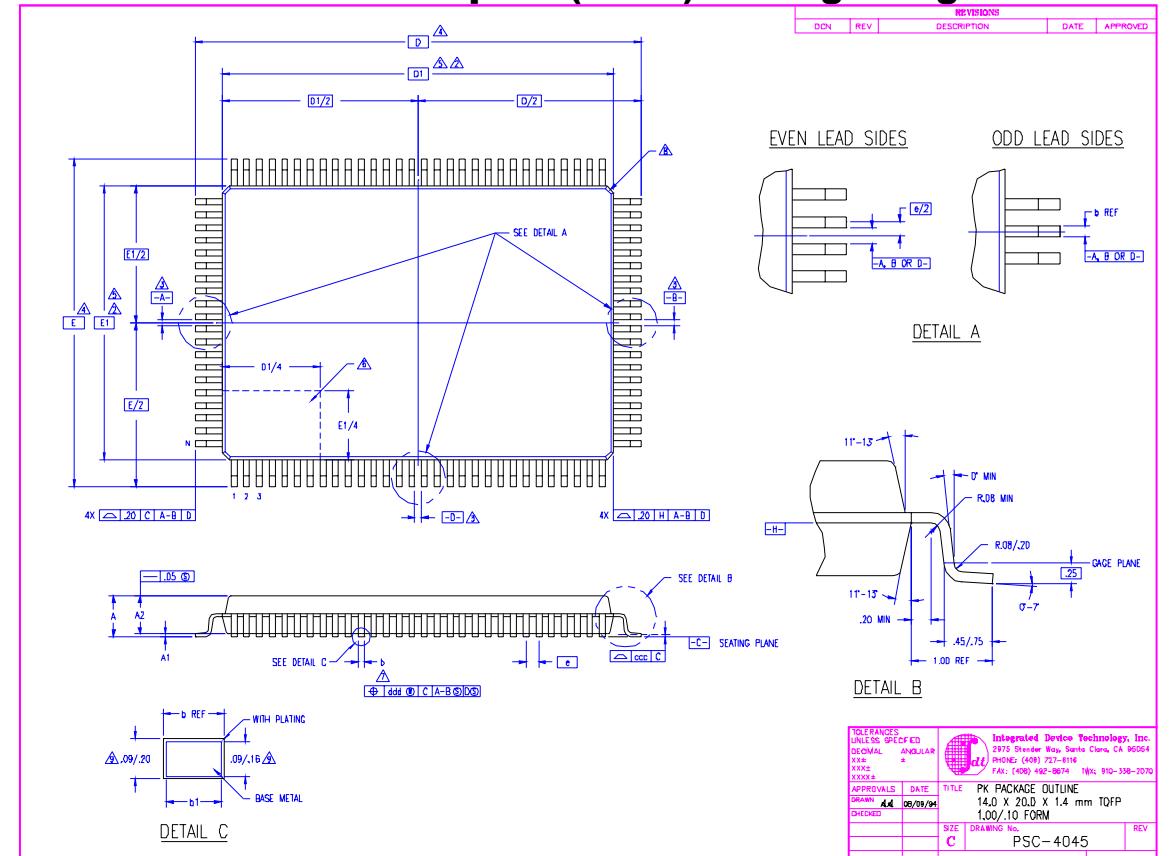
Non-Burst Write Cycle Timing Waveform



NOTES:

1. ZZ input is LOW, \overline{ADV} and \overline{OE} are HIGH, and \overline{LBO} is Don't Care for this cycle.
2. (Ax) represents the data for address Ax, etc.
3. Although only \overline{GW} writes are shown, the functionality of \overline{BWE} and \overline{BWx} together is the same as \overline{GW} .
4. For write cycles, ADSP and ADSC have different limitations.

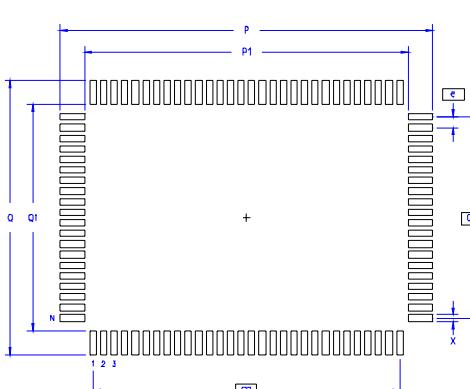
100-Pin Plastic Thin Quad Flatpack (TQFP) Package Diagram Outline



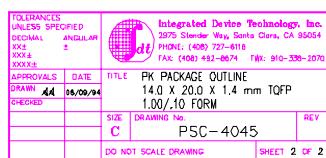
S Y N T R I C L	JEDEC VARIATION		N O T E E
	MIN	NOM	
A	-	.160	
A1	.05	.1D	.15
A2	1.35	1.40	1.45
D	22.00	BSC	4
D1	20.00	BSC	5.2
E	16.00	BSC	4
E1	14.00	BSC	5.2
N	100		
ND	30		
NE	20		
e	.65	BSC	
b	.22	.32	.38
b1	.22	.30	.33
ccc	-	-	.10
ddd	-	-	.13

NOTES.

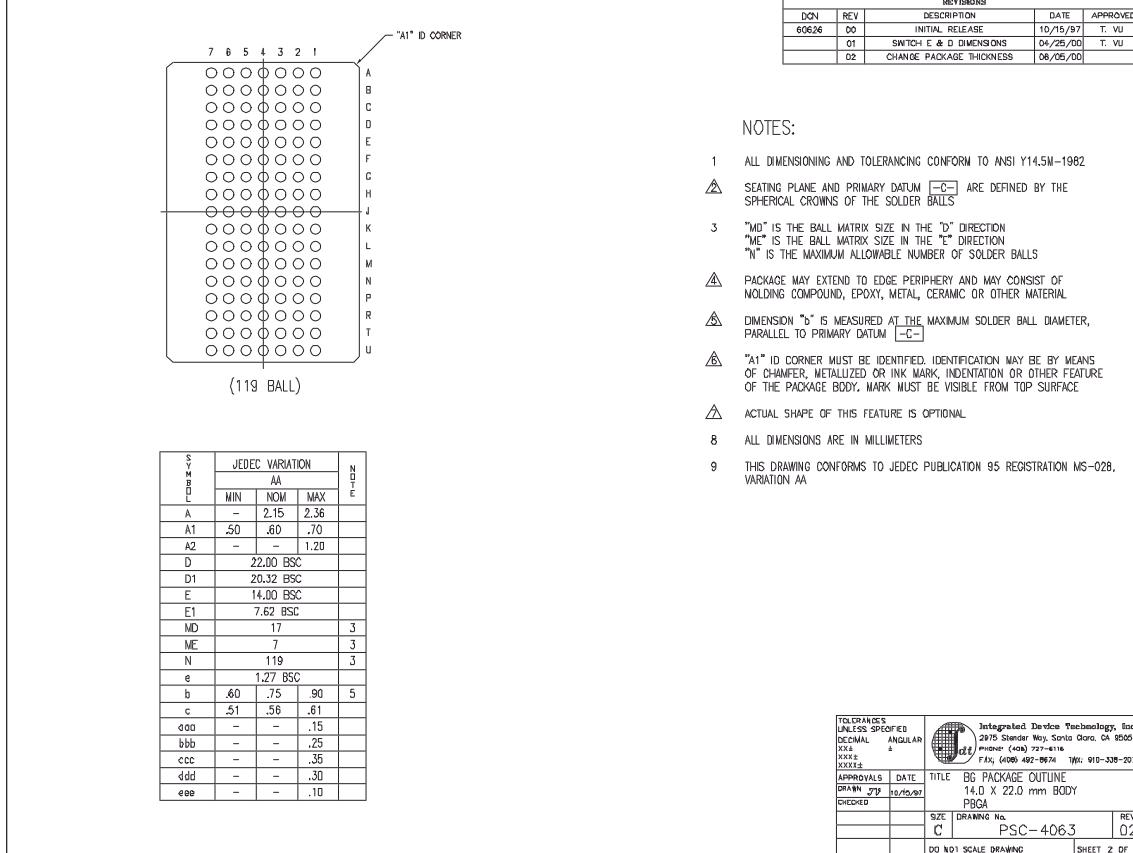
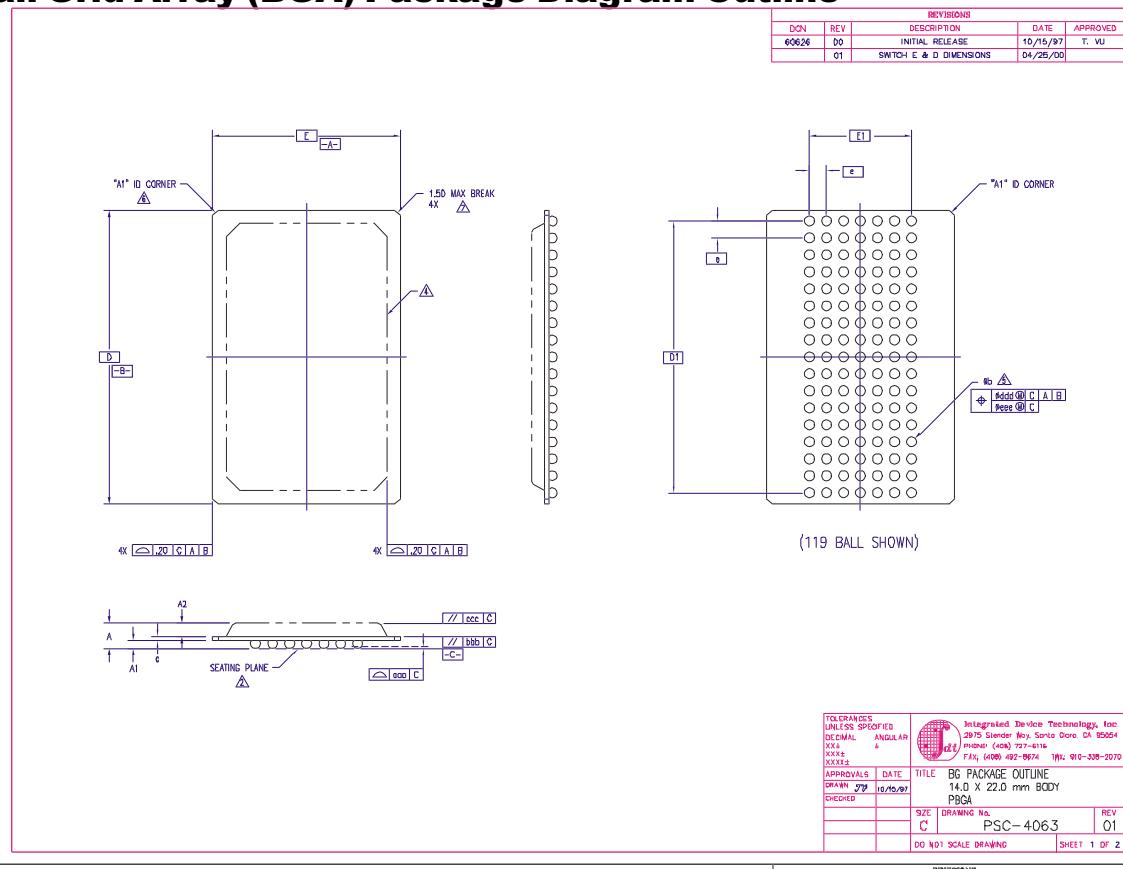
- I ALL DIMENSIONING AND TOLERANCING CONFORM TO ANSI Y14.5M-1982
 - II TDP PACKAGE MAY BE SMALLER THAN BOTTOM PACKAGE BY .15 mm
 - III DATUMS A-B AND D-E TO BE DETERMINED AT DATUM PLANE H-M
 - IV DIMENSIONS D AND E ARE TO BE DETERMINED AT SEATING PLANE C-C
 - V DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE MOLD PROTRUSION IS .25 mm PER SIDE. D1 AND E1 ARE MAXIMUM BODY SIZE DIMENSIONS INCLUDING MOLD MISMATCH
 - VI DETAILS OF PIN 1 IDENTIFIER IS OPTIONAL BUT MUST BE LOCATED WITHIN THE ZONE INDICATED
 - VII DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION IS .08 mm IN EXCESS OF THE b DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT.
 - VIII EXACT SHAPE OF EACH CORNER IS OPTIONAL
 - IX THESE DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .10 AND .25 mm FROM THE LEAD TIP
 - X ALL DIMENSIONS ARE IN MILLIMETERS
 - XI THIS OUTLINE CONFORMS TO JEDEC PUBLICATION 95 REGISTRATION MO-136 VARIATION D AND BX



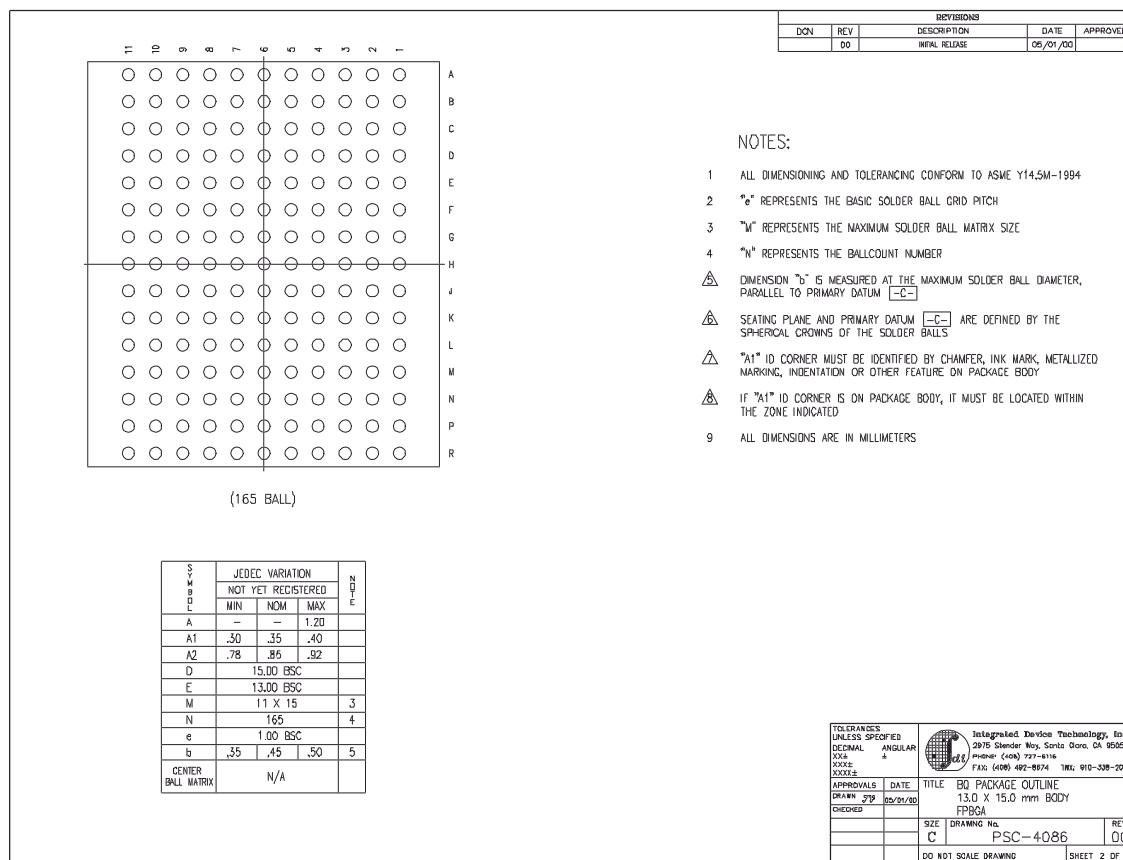
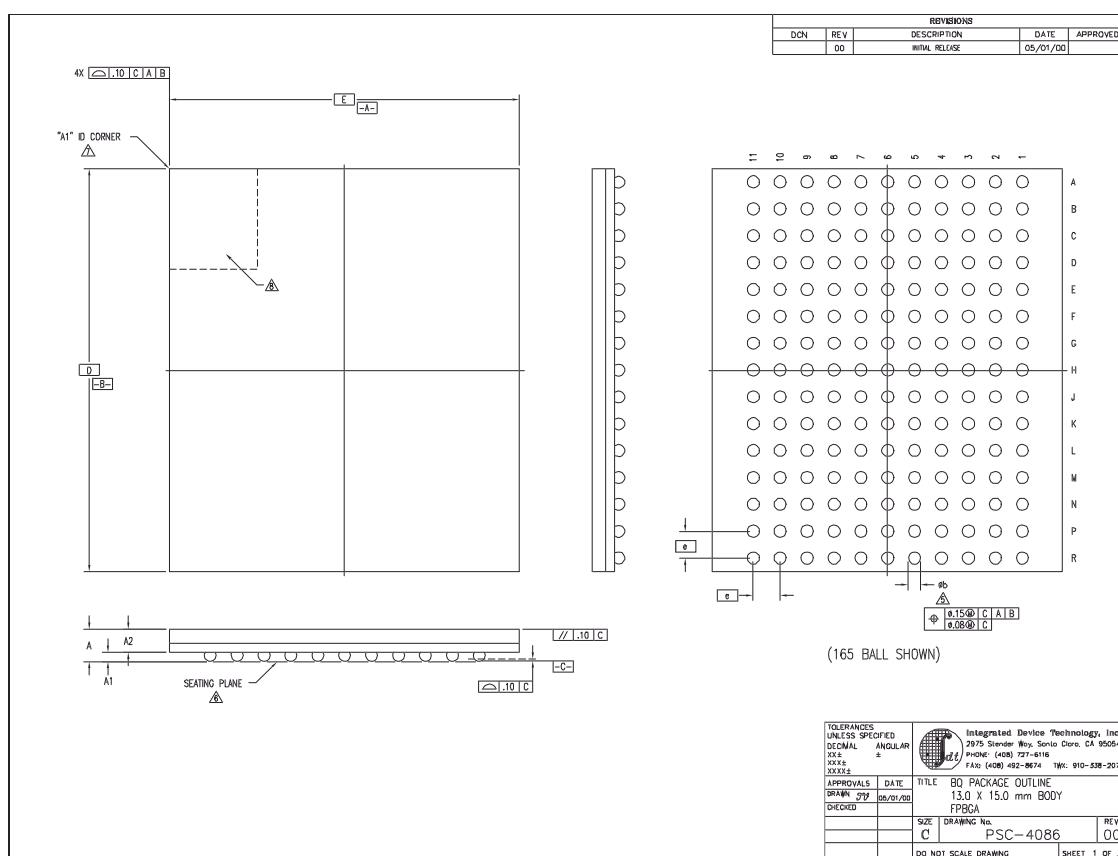
	MIN	MAX
P	22.80	23.00
P1	19.80	20.00
P2	18.85	BSC
Q	16.80	17.00
Q1	13.80	14.00
Q2	12.35	BSC
X	.30	.50
e	.65	BSC
M		150



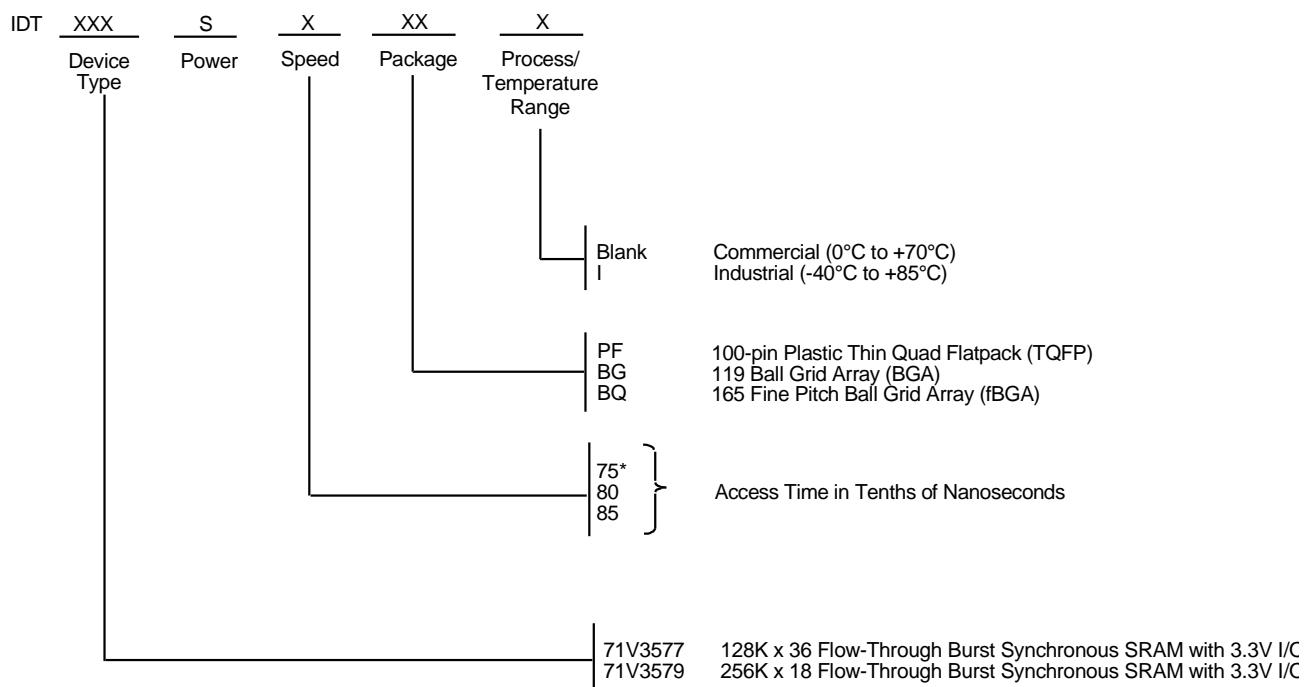
119 Ball Grid Array (BGA) Package Diagram Outline



165 Fine Pitch Ball Grid Array (fBGA) Package Diagram Outline



Ordering Information



5280 drw 12

*Commercial temperature range only.

Datasheet Document History

7/23/99		Updated to new format
9/17/99	Pg. 2	Revised I/O pin description
	Pg. 3	Revised block diagram for flow-through functionality
	Pg. 8	Revised lsb1 and lzz for speeds 7.5 to 8.5ns
	Pg. 18	Added 119-lead BGA package diagram
	Pg. 20	Added Datasheet Document History
12/31/99	Pp. 1, 4, 8, 11, 19	Added Industrial Temperature range offerings
04/03/00	Pg. 18	Added 100pinTQFP Package Diagram Outline
	Pg. 4	Add capacitance table for BGA package; add Industrial temperature to table; Insert note to Absolute Max Ratings and Recommended Operating Temperature tables
06/01/00		Add new package offering, 13 x 15mm 165 fBGA
	Pg. 20	Correct 119BGA Package Diagram Outline
07/15/00	Pg. 7	Add note reference to BG119 pinout
	Pg. 8	Add DNU reference note to BQ165 pinout
	Pg. 20	Update BG119 Package Diagram Outline Dimensions
10/25/00		Remove Preliminary status
	Pg.8	Add reference note to pin N5 on BQ165 pinout, reserved for JTAG <u>TRST</u>
04/22/03	Pg.4	Updated 165 BGA table information from TBD to 7



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